

Supplementary Materials

Electronic transport mechanism for Schottky diodes formed by Au/HVPE a-plane GaN templates grown via in situ GaN nanodot formation

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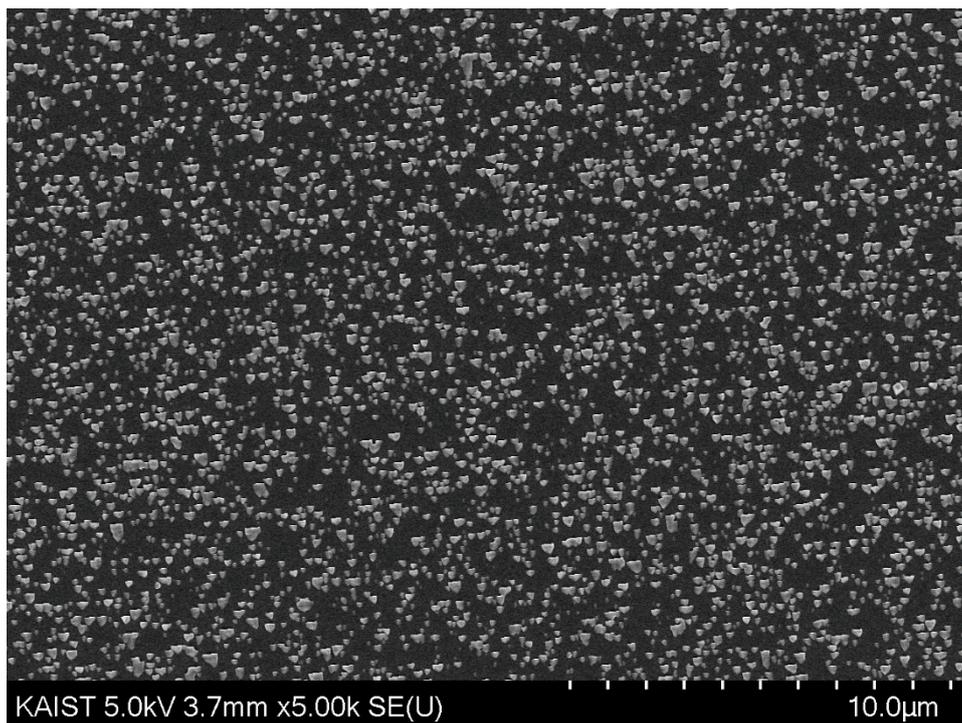


Fig. S1 Plan-view SEM image of a-plane GaN nanodot formed on r-plane sapphire substrate after *in situ* surface treatment.

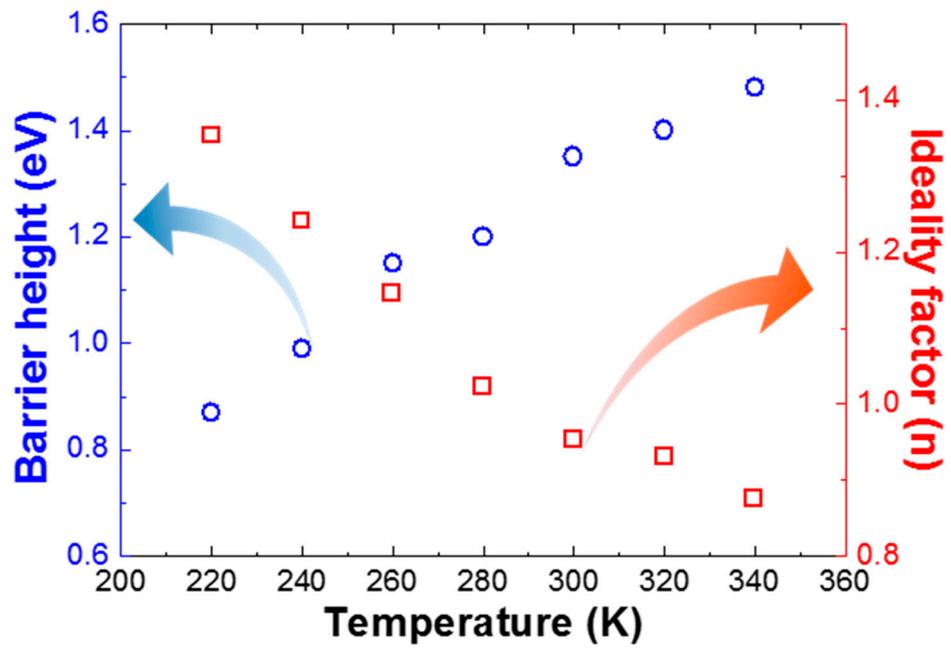


Fig. S2 Barrier height and ideality factor versus temperature in Au/HVPE a-plane GaN templates formed by in situ nanodot formation based on TFE model.